

IN THE SPECIFICATION:

Please replace paragraph [0050] with the following amended paragraph:

[0050] Concurrent with the deposition of the metal layer 502 on the substrate using ECP techniques, selected portions thereof may be polished using EMP techniques, as indicated in step 704 of FIG. 6. During the EMP process, the substrate 22 remains mounted on the ECP/EMP head 64a and immersed in the electrolyte solution used to deposit metal layer 502 thereon. The EMP process in conjunction with the ECP process functions to remove over-plated areas 502a of metal deposited on the dielectric material 602 by alternately applying a potential difference ~~between~~ to the counter electrode c and the working electrode w ~~that is opposite to the polarity used to plate metal on the substrate for ECP.~~

Please replace paragraph [0051] with the following amended paragraph:

[0051] The potential difference applied ~~between~~ to the counter electrode c ~~and the working electrode w~~ for EMP is typically within a range of about 0.2 volts to about 5 volts. The potential difference provides an electrochemical driving force for conductive material resident on the substrate 22 to migrate back into the electrolyte plating solution.

Please replace paragraph [0052] with the following amended paragraph:

[0052] During EMP, the porous pad 28 may contact selective portions of the substrate 22. The porous pad 28 may contact the selective portions of the substrate with a pressure in a range of about 0.1 ~~psi~~ psi and about 5 ~~psi~~ psi. Additionally, the rotatable platen 55 with the porous pad 28 mounted thereon may be rotated at a velocity of about 20 rpm to about 150 rpm.

Please replace paragraph [0053] with the following amended paragraph:

[0053] In the EMP process, the porous pad in conjunction with the electrochemical potential applied between the counter electrode c and the working electrode w provides for highly controllable as well as enhanced polishing rates for polishing the metal layer formed on over-plated areas 502a. The porous pad 28 does not contact the surface of the substrate 22 in locations where localized depressions 504 (vias 602a of FIG. 6b 5a) exist. As such, the rate of polishing is reduced in the localized depressions 504 of the substrate 22 as compared to the contacted portions thereof.